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**INFORMATION DISCLOSURE STATEMENT
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Applicant: MANABE et al.

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Examiner: S. MULPURI

Group Art Unit: 2812

U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR					
	BR					
	CR					
	DR					
	ER					

FOREIGN PATENT DOCUMENTS

	Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
					Enclosed	No	Enclose	No
Sum	FR 58-200527	11/1983	Japan		X			
Sum	GR 60-175468	09/1985	Japan		X			
Sum	HR 63-188938	08/1988	Japan		X			
Sum	IR 02-042770	02/1990	Japan		X			
	JR							
	KR							
	LR							
	MR							

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

Sum	NR	AZOULAY, R. et al., "Mocvd N-Type Doping of GaAs and GaAlAs Using Silicon and Selenium and Fabrication of Double Heterostructure Bipolar Transistor," <i>Journal of Crystal Growth</i> , Vol. 68, 1984, pp. 453-460.						
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	PR	HIRAMATSU, K., "Effects of Buffer Layer in Mowpe Growth of GaN Film on Sapphire Substrate," <i>Nagoya University</i> , 1988, pp. 334-342.						
	QR	KHAN M., "Effect of Si on Photoluminescence of GaN," <i>Solid State Communications</i> , Vol. 57, No. 6, 1986, pp. 405-409.						
	RR	SZE, S., "Physics of Semiconductor Devices," <i>Wiley-Interscience</i> , 1969, pp. 42-43.						
Sum	SR	TIETJEN, J., "Vapor Phase Growth Technique and System for Several III-V Compound Semiconductors," <i>RCA Laboratories</i> , 1969, pp. 1-9.						
	TR							
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	VR							
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Examiner

Date Considered: 5/20/02

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.